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# Silicon Nitride, Silicon Dioxide, and Emerging Dielectrics 11

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## Table of Contents

<i>Preface</i>	<i>iii</i>
<b>Chapter 1</b> <b>Interface Characterization</b>	
Fluctuations in Electronic Properties of MOS Interface in Nanoscale MOSFETs <i>T. Tsuchiya, Y. Morimura, and Y. Mori</i>	3
Electron States in MOS Systems <i>O. Engström</i>	19
Process Engineering and Trap Distribution for Dielectric/Si Interfacial Layer in High-k Gated MOS Devices <i>K. Chang-Liao, C. Fu, C. Lu, Y. Chang, Y. Hsu, C. Tsao, T. Wang, D. Heh, Y. Li, W. Tsai, C. Ai, F. Hou, and Y. Hsu</i>	39
Current Understanding of the Transport Behavior of Hydrogen Species in MOS Stacks and Their Relation to Reliability Degradation <i>Z. Liu, S. Fujieda, H. Ishigaki, M. Wilde, and K. Fukutani</i>	55
Impact of Silicon Nitride Gate Dielectric Composition on the Stability of Low Temperature Nanocrystalline Silicon Thin Film Transistors <i>M. Esmaeili-Rad, G. Chaji, F. Li, M. Moradi, A. Sazonov, and A. Nathan</i>	73
Development of a Fast Technique for Characterizing Interface States <i>L. Lin, Z. Ji, J. Zhang, and W. Zhang</i>	81
Detailed Analysis of Si-SiO <sub>2</sub> Interface Traps in State-of-the-Art MOSFETs Using Charge Pumping <i>D. Bauza</i>	95
Clear Difference between the Chemical Structure of SiO <sub>2</sub> /Si Interfaces Formed Using Oxygen Radicals versus Oxygen Molecules <i>T. Suwa, Y. Kumagai, A. Teramoto, T. Muro, T. Kinoshita, T. Ohmi, and T. Hattori</i>	115

## Chapter 2 Ultra-Thin Film/Reliability

Impact of Twofold Coordinated Nitrogen on the Generation of Deep-Level Hole Traps under Negative-Bias Temperature Stressing <i>C. Gu, D. Ang, and Z. Teo</i>	125
Essential aspects of Negative Bias Temperature Instability (NBTI) <i>A. E. Islam, S. Mahapatra, S. Deora, V. D. Maheta, and M. Alam</i>	145
Atomic Imaging of Atomic H Cleaning of InGAs and InP for ALD <i>W. Melitz, J. Shen, T. Kent, R. Droopad, P. Hurley, and A. C. Kummel</i>	175
Plasma-Assisted Atomic Layer Deposition of Low Temperature SiO <sub>2</sub> <i>G. Dingemans, C. Van Helvoirt, M. Van de Sanden, and W. M. Kessels</i>	191
Surface Passivation of InGaAs/InP HBTs Using Atomic Layer Deposited Al <sub>2</sub> O <sub>3</sub> <i>R. Driad, F. Benkhelifa, L. Kirste, R. Lösch, M. Mikulla, and O. Ambacher</i>	205
Nitric Acid Oxidation Method to Form a Gate Oxide Layer in Sub-Micrometer TFT <i>T. Matsumoto, Y. Kubota, S. Imai, and H. Kobayashi</i>	217
Effects of Deposition Method of PECVD Silicon Nitride as MIM Capacitor Dielectric for GaAs HBT Technology <i>J. Yota</i>	229
Low Temperature Processing of Si-Based Dielectric Thin Films <i>P. Joshi, A. Voutsas, and J. Hartzell</i>	241
Negative Charge in Plasma Oxidized SiO <sub>2</sub> Layers <i>A. Boogaard, A. Y. Kovalgin, and R. Wolters</i>	259
Optical and Electrical Properties of Si-Based Multilayer Structures for Solar Cell Applications <i>R. Nalini, J. Cardin, K. R. Dey, X. Portier, C. Dufour, and F. Gourbilleau</i>	273
Context Dependence Effects in Si/SiON Based Advanced CMOS Devices <i>O. O. Olubuyide</i>	287
Quantitative Discussion on Electron-Hole Universal Tunnel Mass in Ultrathin Dielectric of Oxide and Oxide-Nitride <i>H. Watanabe</i>	303

Physics-Based Hot-Carrier Degradation Modeling	321
<i>S. E. Tyaginov, I. Starkov, H. Enichlmair, J. Park, C. Jungemann, and T. Grasser</i>	
Intrinsic Variability and Reliability in Nano-CMOS	353
<i>J. Velamala, C. Wang, R. Zheng, Y. Ye, and Y. Cao</i>	
Bias-Temperature Instabilities and Radiation Effects on SiC MOSFETs	369
<i>E. Zhang, C. Zhang, D. Fleetwood, R. Schrimpf, S. Dhar, S. Ryu, X. Shen, and S. T. Pantelides</i>	

### **Chapter 3** **Emerging Dielectrics**

Impact of Gate Dielectric Geometry on the Nanowire MOSFETs Performance and Scaling	383
<i>M. Li, W. Cao, D. Huang, C. Shen, S. Cheng, C. Yao, and H. Yu</i>	
Role of Oxygen Transfer for High-k/SiO <sub>2</sub> /Si Stack Structure on Flatband Voltage Shift	403
<i>T. Nabatame, A. Ohi, and T. Chikyow</i>	
Charge Trapping and Reliability Properties of MONOS Memory with High-k Blocking Layer	417
<i>N. Yasuda, S. Fujii, J. Fujiki, and H. Kusai</i>	
Dynamic Negative Bias Stress Instability Effects in Hafnium Silicon Oxynitride and Silicon Dioxide	447
<i>J. Mee, R. Devine, H. Hjalmarson, and K. Kambour</i>	
Electrical and Structural Properties of Ternary Rare-Earth Oxides on Si and Higher Mobility Substrates and their Integration as High-k Gate Dielectrics in MOSFET Devices	461
<i>J. Lopes, E. Durğun Özben, M. Schnee, R. Luptak, A. Nichau, A. Tiedemann, W. Yu, Q. Zhao, A. Besmehn, U. Breuer, M. Luysberg, S. Lenk, J. Schubert, and S. Mantl</i>	
High-k Integration and Interface Engineering for III-V MOSFETs	481
<i>H. Oh, A. B. Sumarlina, and S. Lee</i>	
Plasma Enhanced Atomic Layer Deposition of ZrO <sub>2</sub> : A Thermodynamic Approach	497
<i>E. Blanquet, D. Monnier, I. Nuta, F. Volpi, B. Doisneau, S. Coindeau, J. Roy, B. Detlefs, Y. Mi, J. Zegenhagen, C. Martinet, C. Wyon, and M. Gros-Jean</i>	

V <sub>T</sub> Stability Of High-K/Metal Gate Stacks with Device Scaling in 30nm FDSOI Technology	515
<i>X. Garros, L. Brunet, M. Cassé, O. Weber, F. Andrieu, D. Lafond, C. Gaumer, G. Reibold, and F. Boulanger</i>	
Investigation of Electron and Hole Charge Trapping in LaLuO <sub>3</sub> Stack MOS Capacitor Using the 3-Pulse CV Technique	531
<i>N. Sedghi, I. Mitrovic, J. Lopes, J. Schubert, and S. Hall</i>	
Inelastic Electron Tunneling Spectroscopy (IETS) Study of Ultra-Thin Gate Dielectrics for Advanced CMOS Technology	545
<i>T. Ma</i>	
High-k Gate Dielectric MOSFETs: Meeting the Challenges of Characterization and Modeling	563
<i>M. M. De Souza, S. Sicre, and D. Casterman</i>	
Universal Set/Reset Characteristics of Metal-Oxide Resistance Switching Memories	581
<i>D. Ielmini</i>	
Resistive Switching Behaviors of ReRAM Having W/CeO <sub>2</sub> /Si/TiN Structures	597
<i>C. Dou, K. Mukai, K. Kakushima, P. Ahmet, K. Tsutsui, A. Nishiyama, N. Sugii, K. Natori, T. Hattori, and H. Iwai</i>	
Electrically Detected Magnetic Resonance in Dielectric Semiconductor Systems of Current Interest	605
<i>P. M. Lenahan, C. Cochrane, J. Campbell, and J. Ryan</i>	
Synthesis, Pore Morphology, and Dielectric Property of Mesoporous Low-k Material PSMSQ Using a Reactive High-Temperature Porogen, TEPSS	629
<i>S. Chiu, H. Hsu, M. Che, and J. Leu</i>	
Electrical Characteristics Analysis at "Oxide Flat-Band Voltage" for Al-SiO <sub>2</sub> -Si Capacitor	639
<i>H. Lu, T. Chen, and J. Hwu</i>	
Novel Hardmask for Sub-20nm Copper/Low K Backend Dual Damascene Integration	651
<i>L. Xia, Z. Cui, M. Balseanu, V. Nguyen, K. Zhou, J. Pender, and M. Naik</i>	
Study of Porous SiOCH Patterning Using Metallic Hard Mask: Challenges and Solutions	667
<i>N. Posseme, T. David, T. Chevolleau, M. Darnon, F. Bailly, R. Bouyssou, J. Ducote, H. Chaabouni, M. El Kodadi, C. Licitra, C. Verove, and O. Joubert</i>	
Process Challenges for Integration of Copper Interconnects with Low-k Dielectrics	687
<i>J. Gambino</i>	

Patterning with Amorphous Carbon Thin Films	701
<i>G. A. Antonelli, S. Reddy, P. Subramonium, J. Henri, J. Sims, J. O'loughlin, N. Shamma, D. Schlosser, T. Mounsier, W. Guo, and H. Sawin</i>	
Ultra Low Dielectric Constant Materials for 22 nm Technology Node and Beyond	717
<i>M. R. Baklanov, E. A. Smirnov, and L. Zhao</i>	
Development of Porosimetry Techniques for the Characterization of Plasma-Treated Porous Ultra Low-k Materials	729
<i>C. Licitra, T. Chevolleau, R. Bouyssou, M. El Kodadi, G. Haberfehlner, J. Hazart, L. Viot, M. Besacier, N. Posseme, M. Darnon, R. Hurand, P. Schiavone, and F. Bertin</i>	
An Electron Paramagnetic Resonance Study of Defects in Interlayer Dielectrics	747
<i>B. C. Bittel, T. Pomorski, P. M. Lenahan, and S. King</i>	
Development of Voltammetry-Based Techniques for Characterization of Porous Low-k/Cu Interconnect Integration Reliability	757
<i>C. Kim, L. Chen, N. Michael, W. Bang, Y. Park, T. Ryan, and S. King</i>	
Recent Findings in Electrical Behavior of CMOS High-K Dielectric/Metal Gate Stacks	773
<i>G. Ghibaudo, J. Coignus, M. Charbonnier, J. Mitard, C. Leroux, X. Garros, R. Clerc, and G. Reimbold</i>	
Flatband Voltage Tuning of HfSiON-Based Gate Stacks: Impact of High Temperature Activation Annealing and LaO <sub>x</sub> Capping Layers	805
<i>R. Boujamaa, S. Baudot, E. Martinez, O. Renault, B. Detlefs, J. Zegenhagen, V. Loup, F. Martin, M. Gros-Jean, F. Bertin, and C. Dubourdieu</i>	
Physical and Electrical Effects of the Dep-Anneal-Dep-Anneal (DADA) Process for HfO <sub>2</sub> in High K/Metal Gate Stacks	815
<i>R. D. Clark, S. Aoyama, S. Consiglio, G. Nakamura, and G. Leusink</i>	
Interface Structure and Charge Trapping in Hf-Incorporated Y <sub>2</sub> O <sub>3</sub> Gate Dielectrics on Germanium	835
<i>C. Mahata, S. Mallik, T. Das, M. Hota, and C. Maiti</i>	

#### **Chapter 4** **Poster Session**

Schottky Barrier Height at Dielectric Barrier/Cu Interface in Low-K/Cu Interconnects	849
<i>S. King, M. French, M. Jaehnig, M. Kuhn, and B. French</i>	

Global and Local Stress Characterization of SiN/Si(100) Wafers Using Optical Surface Profilometer and Multiwavelength Raman Spectroscopy <i>W. Yoo, J. Kajiwara, T. Ueda, T. Ishigaki, and K. Kang</i>	861
Mechanisms of Difficulty to Correlate the Leakage Current of High-k Capacitor Structures with Defect States Detected Spectroscopically by the Thermally Stimulated Current Technique <i>W. S. Lau</i>	873
Degradation Mechanisms of MILC P-Channel Poly-Si TFTs under Dynamic Hot-Carrier Stress Using a Novel Test Structure <i>C. Lin, W. Hong, T. Lin, H. Lin, and T. Huang</i>	889
Solution Processed High-k Lanthanide Oxides for Low Voltage Driven Transparent Oxide Semiconductor Thin Film Transistors <i>S. Choi, B. Park, M. Jang, S. Jeong, J. Lee, B. Ryu, T. Seong, and H. Jung</i>	901
Reliability Properties and Current Conduction Mechanisms of HfO <sub>2</sub> MIS Capacitor with Dual Plasma Treatment <i>K. Chang, T. Chang, S. Chen, and I. Deng</i>	909
A MIM Diode with Ultra Abrupt Switching Process and High On/Off Current Ratio <i>L. Zhang and R. Huang</i>	923
Author Index	931